Industrial galvanic isolated gate driver ICs
Selection guide 2018

www.infineon.com/gatedriver
www.infineon.com/1EDcompact
EiceDRIVER™ 1ED Compact gate driver IC family
1200 V galvanically isolated compact gate driver ICs

Infineon’s new EiceDRIVER™ 1ED Compact 300 mI family is recognized under UL 1577 with an insulation test voltage of (Vg = 2500 Vrms) for 1 min. The functional isolated EiceDRIVER™ 1ED Compact 150 mI and 300 mI families are also available.
The EiceDRIVER™ 1ED Compact family is the perfect driver for super junction MOSFETs such as CoolMOS™, IGBTs, Silicon Carbide (SiC) MOSFET such as CoolSiC®, and IGBT modules.

Product Features
- Available in DSO-8-300 mI wide body package with 8 mm crepage distance and DSO-8-150 mI
- Up to 10 x higher peak rail-to-output
- Suitable for operation at high ambient temperature
- Separate source and sink outputs or active Miller clamp
- Short circuit clamping and active shutdown
- ≥ 100 kV/µs CMTI

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EiceDRIVER™ Enhanced gate driver IC family
1200 V galvanically isolated enhanced gate driver ICs

The EiceDRIVER™ Enhanced gate driver ICs are galvanic isolated single channel IGBT and SiC MOSFET drivers in DSO-16 package that provide output current capabilities of typically ≥ 2 A. The precision DESAT function is an excellent solution for SiC MOSFET short-circuit protection. All logic pins are 5 V CMOS compatible. 2ED02012-F2 is the dual-channel version of 1ED02012-F2 in DSO-36 package. 2ED02012-F1 is a high voltage, high speed power MOSFET and IGBT driver with interlocking high and low side referenced outputs.

Product Features
- Available in wide body package with 8 mm crepage distance
- Suitable for operation at high ambient temperature
- Active Miller clamp
- Short circuit clamping and active shutdown
- ≥ 100 kV/µs CMTI
- Precision DESAT protection

www.infineon.com/EiceDRIVER-enhanced

Coreless Transformer (CT) Technology
Galvanically isolated EiceDRIVER™ ICs based on our coreless transformer (CT) technology which uses semiconductor manufacturing processes to integrate an on-chip transformer consisting of metal spirals and silicon oxide insulation. The on-chip transformers are used for transmitting switching information between input chip and output chip which are galvanically isolated.

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Gate Driver Support Tools
- Infineon Gate Drivers Home Page
- Simulation Tools
- Gate Driver X-Reference
- Gate Driver Selection Guide Brochure
- Gate Driver Finder Tool

www.infineon.com/gatedriver
www.infineon.com/eddesigner
www.infineon.com/crs
www.infineon.com/gdbrochure
www.infineon.com/gdfinder

Driving SiC MOSFETs
Every isolated EiceDRIVER™ IC is well-suited to drive SiC MOSFETs such as the ultra-fast switching 1200-V CoolSiC™ power MOSFETs. The drivers incorporate most important key features and parameters for SiC driving such as tight propagation delay matching, precise input filters, wide output-side supply range, negative gate voltage capability or Miller clamping, and extended CMI capability.

www.infineon.com/SiC-gd
www.infineon.com/SiC-MOS
Service hotline

Infineon offers its toll-free 0800/4001 service hotline as one central number, available 24/7 in English, Mandarin and German.

› Germany .................. 0800 951 951 951 (German/English)
› China, mainland .......... 4001 200 951 (Mandarin/English)
› India .......................... 000 800 4402 951 (English)
› USA ............................ 1-866 951 9519 (English/German)
› Other countries ......... 00* 800 951 951 951 (English/German)
› Direct access ............. +49 89 234-0 (interconnection fee, German/English)

* Please note: Some countries may require you to dial a code other than “00” to access this international number.
Please visit www.infineon.com/service for your country!